

M2D-1200-0160

Silicon Carbide MOSFET Bare Die

N-channel Enhancement Mode

Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness
- Halogen Free, RoHS Compliant

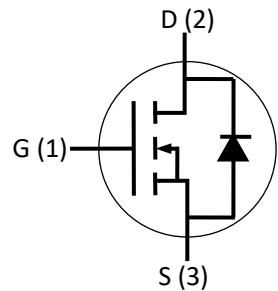
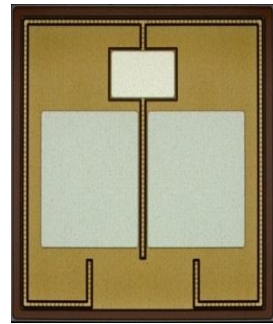
Benefits

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power applications

Package



Part Number	Die Size
M2D-1200-0160	2.40*2.65

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V	$V_{GS}=0V, I_D=100\mu A$	
V_{GSmax}	Gate - Source Voltage	-10/+25	V	Absolute maximum values	
V_{GSop}	Gate - Source Voltage	-5/+20	V	Recommended operational values	
I_D	Continuous Drain Current	17	A	$V_{GS}=20V, T_C=25^\circ\text{C}$	
		11		$V_{GS}=20V, T_C=100^\circ\text{C}$	
I_{DM}	Pulse Drain Current	38	A	Pulse width limited by T_{jmax}	
P_D	Power Dissipation	127	W	$T_C=25^\circ\text{C}, T_J=150^\circ\text{C}$	
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$		

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Electrical Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	$V_{GS}=0V, I_D=100\mu A$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.4	4.0	V	$V_{GS}=V_{DS}, I_{DS}=2.5mA, T_C=25^\circ C$	
			1.8			$V_{GS}=V_{DS}, I_{DS}=2.5mA, T_C=150^\circ C$	
I_{DSS}	Zero Gate Voltage Drain Current		1	100	μA	$V_{DS}=1200V, V_{GS}=0V$	
I_{GSS}	Gate-Source Leakage Current		20	200	nA	$V_{GS}=20V, V_{DS}=0V$	
$R_{DS(on)}$	Drain-Source on-state Resistance		160	192	m Ω	$V_{GS}=20V, I_D=10A, T_C=25^\circ C$	
			285			$V_{GS}=20V, I_D=10A, T_C=150^\circ C$	
g_{fs}	Transconductance		4.2		S	$V_{GS}=20V, I_D=10A, T_J=25^\circ C$	
			4.0			$V_{GS}=20V, I_D=10A, T_J=150^\circ C$	
C_{iss}	Input Capacitance		950		pF	$V_{GS}=0V, V_{DS}=1000V, f=1MHz$ $V_{AC}=25mV$	
C_{oss}	Output Capacitance		35.0				
C_{rss}	Reverse Transfer Capacitance		8.5				
E_{ON}	Turn-On Switching Energy		95		μJ	$V_{DS}=800V, V_{GS}=-5/20V, I_D=10A,$ $R_{G(ext)}=2.5\Omega, L=256\mu H$	
E_{OFF}	Turn-Off Switching Energy		48				
$t_{d(on)}$	Turn-On Delay Time		12		ns	$V_{DD}=800V, V_{GS}=-5/20V$ $I_D=10A, R_{G(ext)}=2.5\Omega,$ $R_L=80\Omega, \text{Timing relative to } V_{DS}$	
t_r	Rise Time		20				
$t_{d(off)}$	Turn-Off Delay Time		15				
t_f	Fall Time		10				
$R_{G(int)}$	Internal Gate Resistance		5.8		Ω	$f=1MHz, V_{AC}=25mV$	
Q_{gs}	Gate to Source Charge		9		nC	$V_{DD}=800V, V_{GS}=-5/20V$ $I_D=10A$	
Q_{gd}	Gate to Drain Charge		17				
Q_g	Total Gate Charge		42				

Reverse Diode Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	3.5		V	$V_{GS}=-5V, I_{SD}=5A, T_J=25^\circ C$	
		3.3		V	$V_{GS}=-5V, I_{SD}=5A, T_J=150^\circ C$	
I_S	Continuous Diode Forward Current		17	A	$T_C=25^\circ C$	
t_{rr}	Reverse Recovery time	27		ns	$V_{GS}=-5V, I_{SD}=10A, V_R=800V,$ $dif/dt=1000A/\mu s;$	
Q_{rr}	Reverse Recovery Charge	123		nC		
I_{rrm}	Peak Reverse Recovery Current	8.5		A		

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Mechanical Parameters

Parameter	Typ.	Unit
Die Size	2.40 x 2.65	mm
Source Pad Size	1.40*0.75	mm
Gate Pad Size	0.80*0.50	mm
Thickness	180± 10%	μm
Wafer Size	150	mm
Top SideMetalization (Al)	4	μm
Bottom SideMetalization (Ni/Ag)	1.5	μm

